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30BQ015PbF

RoH^S

COMPLIANT

Vishay High Power Products

Schottky Rectifier, 3.0 A



- 125 °C T_J operation ($V_R < 5 V$)
- Optimized for OR-ing applications
- Ultra low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Lead (Pb)-free ("PbF" suffix)
- Designed and qualified for industrial level

DESCRIPTION

The 30BQ015PbF surface mount Schottky rectifier has been designed for applications requiring low forward drop and very small foot prints on PC boards. The proprietary barrier technology allows for reliable operation up to 125 °C junction temperature. Typical applications are in disk drives, switching power supplies, converters, freewheeling diodes, battery charging, and reverse battery protection.

MAJOR RATINGS AND CHARACTERISTICS					
SYMBOL	CHARACTERISTICS	VALUES	UNITS		
I _{F(AV)}	Rectangular waveform	3.0	A		
V _{RRM}		15	V		
I _{FSM}	$t_p = 5 \ \mu s \ sine$	650	A		
V _F	1.0 Apk, T _J = 75 °C	0.30	V		
TJ	Range	- 55 to 125	°C		

VOLTAGE RATINGS				
PARAMETER	SYMBOL	30BQ015PbF	UNITS	
Maximum DC reverse voltage	V _R	15	V	
Maximum working peak reverse voltage	V _{RWM}	25	v	

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Movimum overage forward ourrest		50 % duty cycle at T_L = 83 °C, re	T _L = 83 °C, rectangular waveform		
Maximum average forward current	I _{F(AV)}	50 % duty cycle at T_L = 78 °C, rectangular waveform		4.0	
Maximum peak one cycle non-repetitive surge current	I _{FSM}	5 µs sine or 3 µs rect. pulse	Following any rated load condition and with rated V _{RRM} applied	650	A
		10 ms sine or 6 ms rect. pulse		75	
Non-repetitive avalanche energy	E _{AS}	T _J = 25 °C, I _{AS} = 0.5 A, L = 12 mH		1.5	mJ
Repetitive avalanche current	I _{AR}	Current decaying linearly to zero in 1 μ s Frequency limited by T _J maximum V _A = 1.5 x V _R typical		0.5	А

For technical questions, contact: diodes-tech@vishay.com

* Pb containing terminations are not RoHS compliant, exemptions may apply



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SMC

PRODUCT SUMMARY				
I _{F(AV)}	3.0 A			
V _R	15 V			
I _{RM}	50 mA at 100 °C			

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ELECTRICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum forward voltage drop	V _{FM} ⁽¹⁾	3 A	T _J = 25 °C	0.35	v
		6 A		0.40	
		3 A	- T _J = 75 °C	0.30	
		6 A		0.35	
Mar dan an a	I _{RM} ⁽¹⁾	T _J = 25 °C	V _R = Rated V _R	4	mA
Maximum reverse leakage current		T _J = 100 °C		50	
Maximum junction capacitance	CT	$V_{\rm R}$ = 5 $V_{\rm DC}$ (test signal range 100 kHz to 1 MHz) 25 °C		1120	pF
Typical series inductance	L _S	Measured lead to lead 5 mm from package body		3.0	nH
Maximum voltage rate of change	dV/dt	Rated V _R		10 000	V/µs

Note

⁽¹⁾ Pulse width < 300 μ s, duty cycle < 2 %

THERMAL - MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum junction temperature range	T _J ⁽¹⁾		- 55 to 125	°C	
Maximum storage temperature range	T _{Stg}		- 55 to 150	-0	
Maximum thermal resistance, junction to lead	R _{thJL} ⁽²⁾		12	°C/W	
Maximum thermal resistance, junction to ambient	R _{thJA}	DC operation	46		
Approvimete weight			0.24	g	
Approximate weight			0.008	OZ.	
Marking device		Case style SMC (similar to DO-214AB)	V3	V3C	

Notes

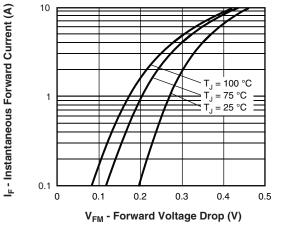
 $^{(1)} \quad \frac{dP_{tot}}{dT_J} < \frac{1}{R_{thJA}} \quad \text{thermal runaway condition for a diode on its own heatsink}$

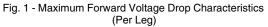
(2) Mounted 1" square PCB

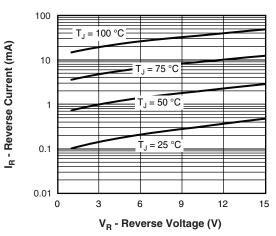


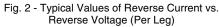
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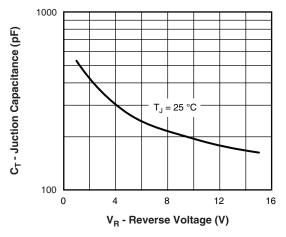


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage (Per Leg)

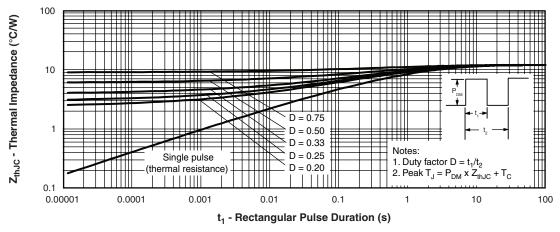
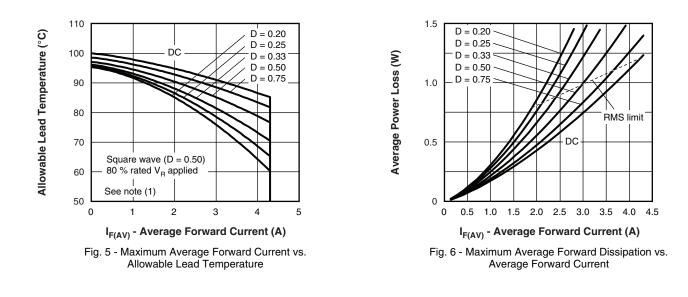


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics (Per Leg)

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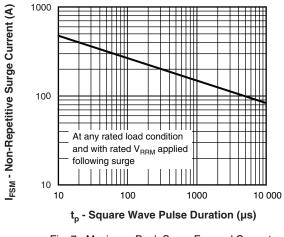


Fig. 7 - Maximum Peak Surge Forward Current vs. Pulse Duration

Note

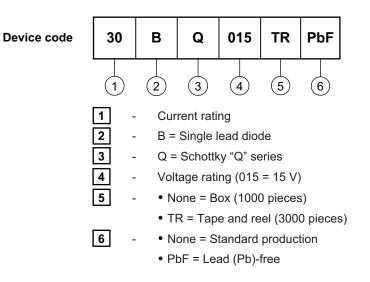
- (1) Formula used: $T_C = T_J (Pd + Pd_{REV}) \times R_{thJC};$ $Pd = Forward power loss = I_{F(AV)} \times V_{FM} at (I_{F(AV)}/D)$ (see fig. 6); $Pd_{REV} = Inverse power loss = V_{R1} \times I_R (1 D); I_R at V_{R1} = 80 \% rated V_R$



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ORDERING INFORMATION TABLE



LINKS TO RELATED DOCUMENTS			
Dimensions http://www.vishay.com/doc?95023			
Part marking information	http://www.vishay.com/doc?95029		
Packaging information	http://www.vishay.com/doc?95034		



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